

Fairchild's Board of Directors announces:

Foundation of Technology Development Centre for High-Voltage Semiconductors in Munich

The mission of this team is to advance Fairchild's Technology and product portfolio for High Voltage applications for Industrial, Automotive and Consumer markets to take over the leading edge position.

This newly formed R&D centre, located in Munich, provides opportunities to their members to closely work with existing global Fairchild Technologists in US, Sweden and Korea, as well as to work in partnerships with Research institutes and hand selected partnership programs with competitors.

The scope of this team includes

- ⇒ Device and process simulation
- ⇒ Design and layout experts
- ⇒ Characterization and testing lab
- ⇒ Experts for process integration, device architecture, novel materials and module development

For the initial phase, we have opened positions for:

Device Simulation Experts

Job description:

You are responsible to develop and optimize device architecture for Fairchild's next generation IGBT generations, optimize static and dynamic device performance and work with local and Korean process experts to create prototypes.

Job requirement:

We are looking for highly innovative and self-motivated individuals, Master or PhD degree in Electrical engineering, Physics or similar, fluency in English required. At least 4 years experience in High Voltage Discrete device development, using state of the art simulation software, preferably Synopsis TCAD process and device simulators. Solid knowledge of state-of-the-art IGBT device architecture required. 3D simulation, device layout experience and packaging know-how is of advantage but not mandatory.

Device Modelling Experts

Job description:

You will be spearheading a team for device parameter extraction and modelling including behavioural and (semi)-mathematical models for High Voltage devices. Near term emphasis is put on Trench IGBT and Superjunction MOSFET developments.

Job requirement:

We are looking for highly innovative and self-motivated individuals with Master or PhD degree in Electrical engineering, Physics or similar; fluency in English required. At least 3 years experience in High Voltage device test keys drawings, parameter extraction and device modelling. PSPICE - equivalent circuit and knowledge of electro-thermal behaviour for Power devices is required. Device layout experience would be beneficial.

IGBT Technologist

Job description:

You will be shaping a global team with the distinct focus in IGBT development, focussing on device architecture, new process modules and innovative package solutions for automotive and industrial applications.

Job requirement:

We are looking for a senior technology expert with Master or PhD degree in Electrical engineering, Physics or similar with profound semiconductor background in the field of high-voltage technology. You need to have at least 10 years experience in IGBT development, wide knowledge of process, device and package topics. Experience with HV-MOSFETS, Superjunction, GTO's or IGCT's as well as experience on specific automotive and industrial applications will be preferred.

We offer:

- ⇒ Start-up spirit in highly inspirational and expanding team in Muenchen
- ⇒ Space for fundamental and scientific research
- ⇒ Very competitive, performance oriented compensation schemes
- ⇒ High strategic impact and visibility within a global company

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